

Product Summary

BV_{DSS}	$R_{DS(ON) max}$	I_D $T_C = +25^\circ C$
700V	0.6Ω @ $V_{GS} = 10V$	8A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Adaptor
- LCD & PDP TV
- Lighting

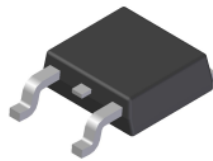
Features

- Low Gate Input Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

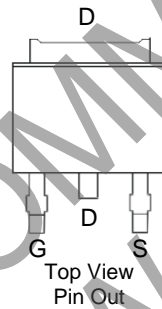
Mechanical Data

- Case: TO252 (DPAK) (Type TH)
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)

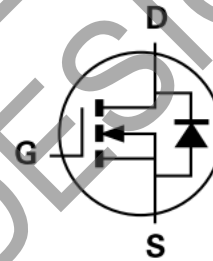
TO252 (DPAK) (Type TH)



Top View



Top View
Pin Out



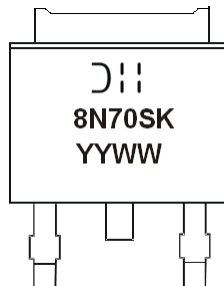
Internal Schematic

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMJ70H601SK3-13	Standard	TO252 (DPAK) (Type TH)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- ⌋:: = Manufacturer's Marking
 8N70SK = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 = 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	700	V
Gate-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = 10V	I _D	T _C = +25°C	8
		T _C = +100°C	6.4
Maximum Body Diode Forward Current (Note 6)	I _S	4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	15	A
Avalanche Current (Note 7)	I _{AS}	L = 60mH	1.7
Avalanche Energy (Note 7)		L = 60mH	86
Peak Diode Recovery dv/dt (Note 7)	dv/dt	7	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _C = +25°C	125
		T _C = +100°C	50
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	72	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	1.0	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	700	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 700V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±30V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	3.4	4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.5	0.6	Ω	V _{GS} = 10V, I _D = 2.1A
Diode Forward Voltage	V _{SD}	—	0.85	1.3	V	V _{GS} = 0V, I _S = 2.1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{ISS}	—	686	—	pF	V _{DS} = 50V, f = 1MHz, V _{GS} = 0V
Output Capacitance	C _{OSS}	—	267	—		
Reverse Transfer Capacitance	C _{RSS}	—	8	—		
Gate Resistance	R _G	—	2.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	20.9	—	nC	V _{DD} = 560V, I _D = 8A, V _{GS} = 10V
Gate-Source Charge	Q _{gs}	—	3.0	—		
Gate-Drain Charge	Q _{gd}	—	9.4	—		
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = 350V, V _{GS} = 10V, R _G = 4.7Ω, I _D = 8A
Turn-On Rise Time	t _r	—	23	—		
Turn-Off Delay Time	t _{D(OFF)}	—	32	—		
Turn-Off Fall Time	t _f	—	17	—		
Body Diode Reverse Recovery Time	t _{RR}	—	261	—	ns	I _S = 8A, di/dt = 100A/µs
Body Diode Reverse Recovery Time (T _J = +150°C)	t _{RR}	—	337	—	ns	
Body Diode Reverse Recovery Charge	Q _{RR}	—	3.0	—	µC	
Body Diode Reverse Recovery Charge (T _J = +150°C)	Q _{RR}	—	4.0	—	µC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 7. Guaranteed by design. Not subject to production testing.
 8. Short duration pulse test used to minimize self-heating effect.

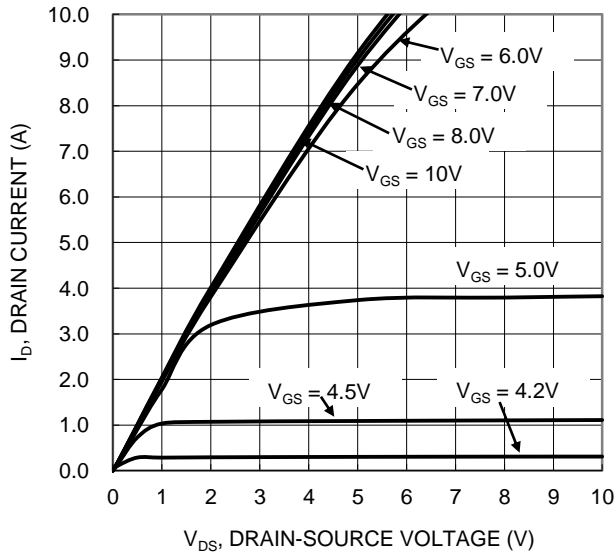


Figure 1. Typical Output Characteristic

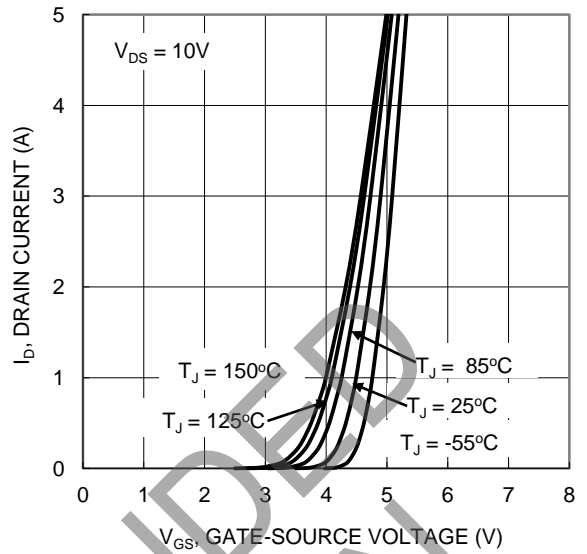


Figure 2. Typical Transfer Characteristic

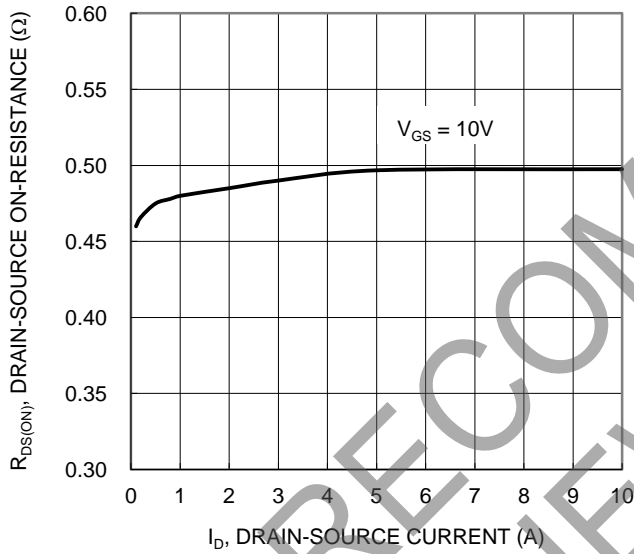


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

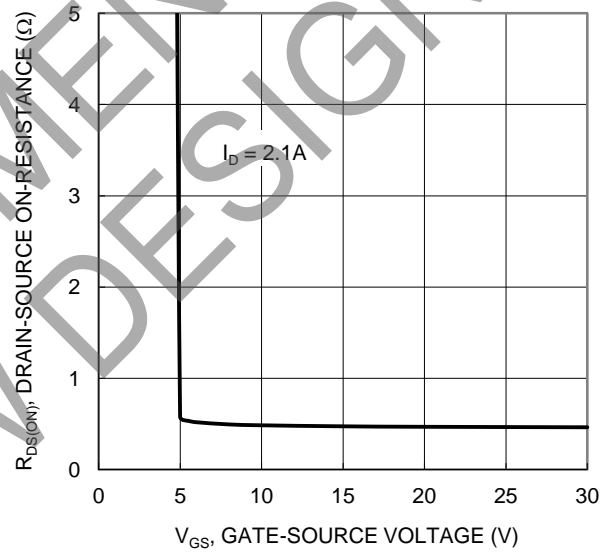


Figure 4. Typical Transfer Characteristic

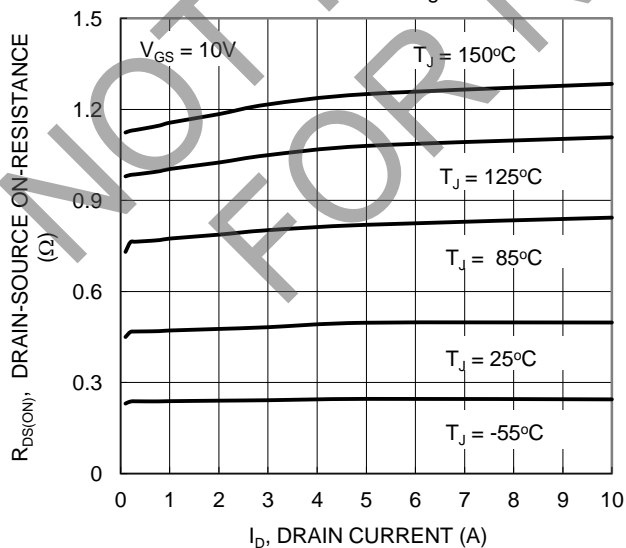


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

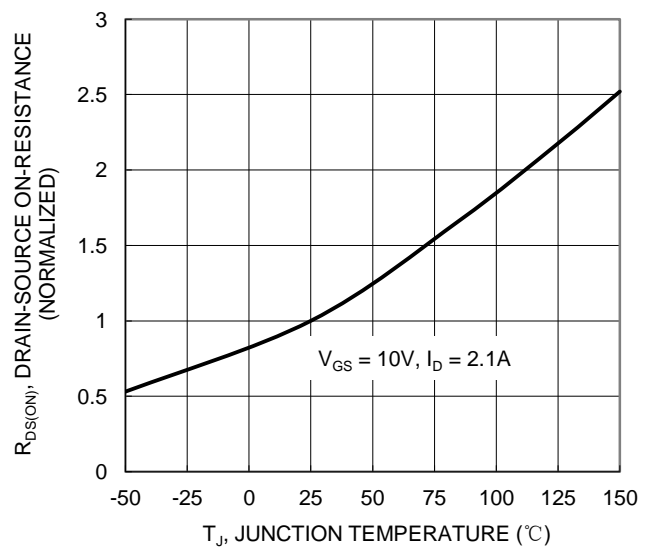


Figure 6. On-Resistance Variation with Temperature

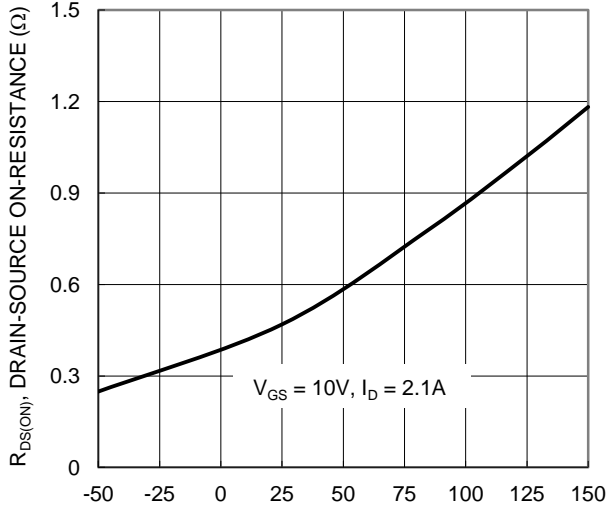


Figure 7. On-Resistance Variation with Temperature

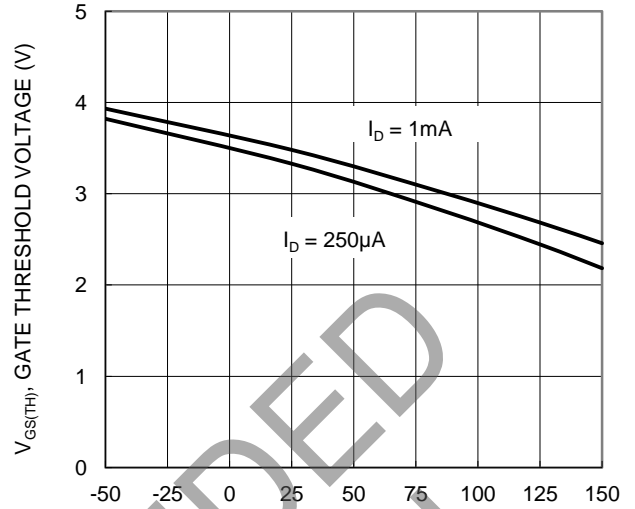


Figure 8. Gate Threshold Variation vs. Junction Temperature

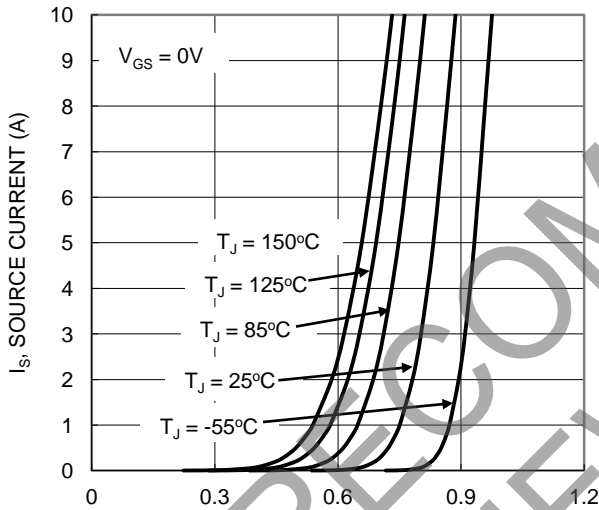


Figure 9. Diode Forward Voltage vs. Current

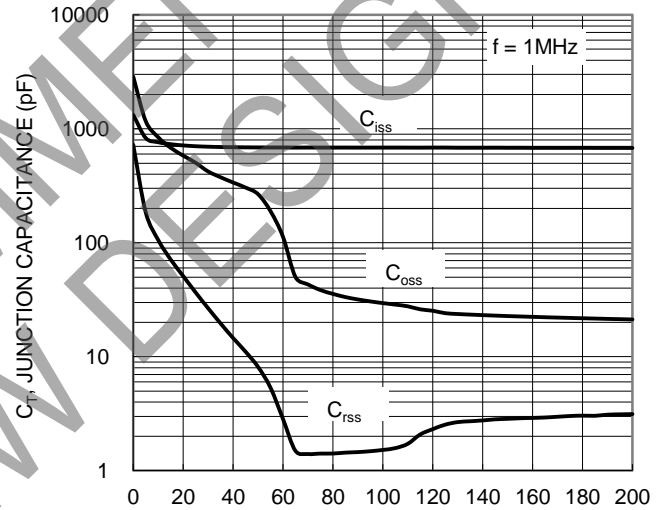


Figure 10. Typical Junction Capacitance

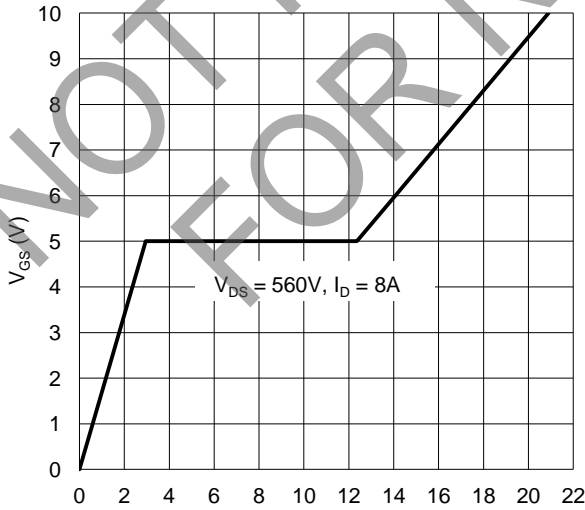


Figure 11. Gate Charge

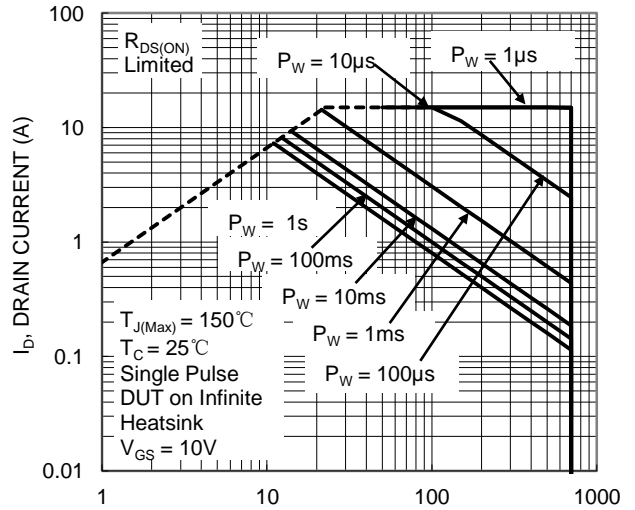


Figure 12. SOA, Safe Operation Area

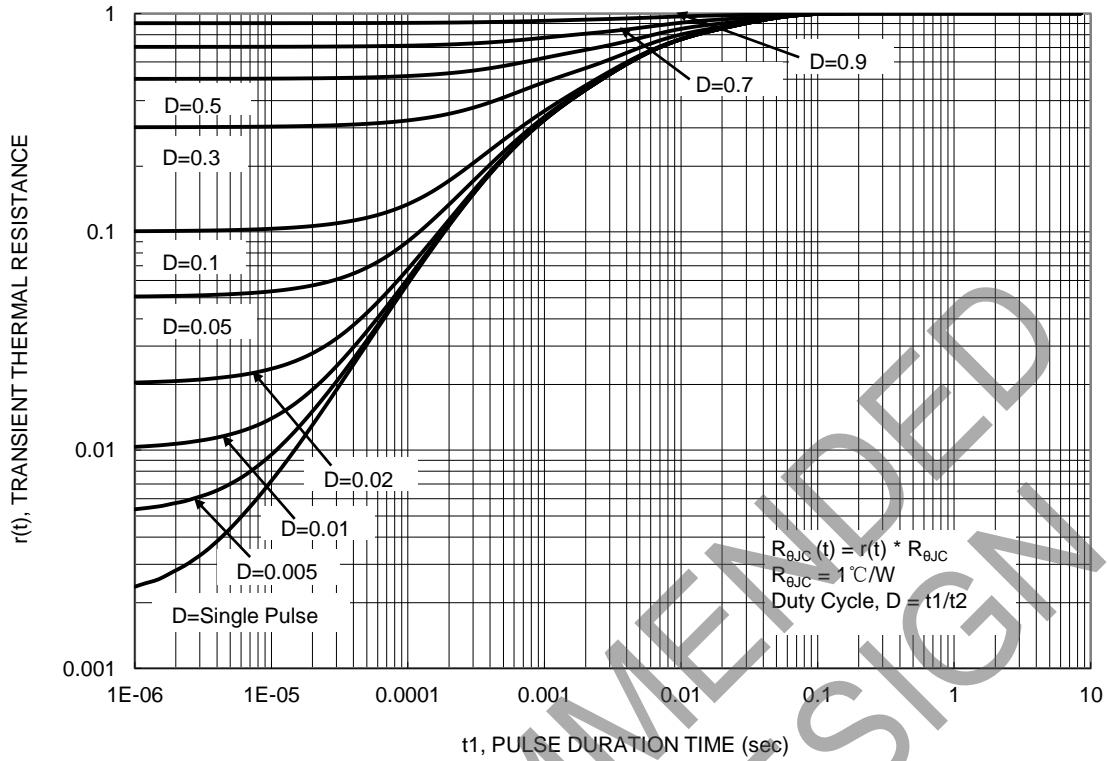


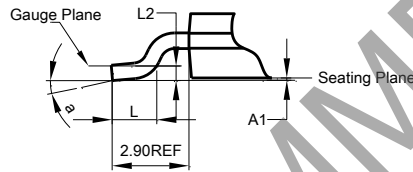
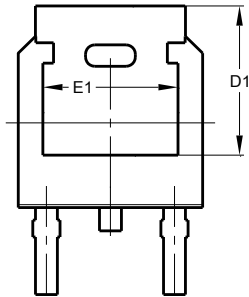
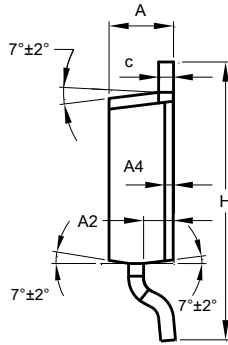
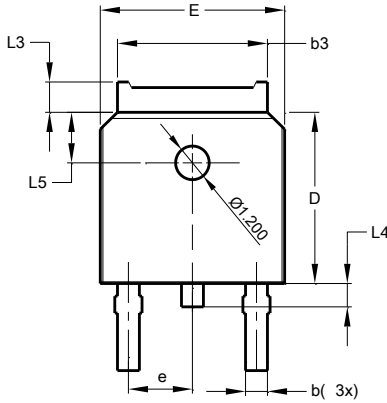
Figure 13. Transient Thermal Resistance

NOT RECOMMENDED FOR NEW DESIGN

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK) (Type TH)

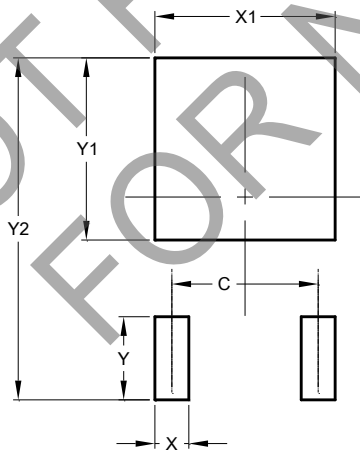


TO252 (DPAK) (Type TH)			
Dim	Min	Max	Typ
A	2.20	2.38	2.30
A1	0.00	0.10	-
A2	0.97	1.17	1.07
A4		0.10	REF
b	0.72	0.85	0.78
b3	5.23	5.45	5.33
c	0.47	0.58	0.53
D	6.00	6.20	6.10
D1		5.30	REF
e		2.286	BSC
E	6.50	6.70	6.60
E1	4.70	4.92	4.83
H	9.90	10.10	10.30
L	1.40	1.70	1.60
L2		0.51	BSC
L3	0.90	1.25	-
L4	0.60	1.00	0.80
L5	1.70	1.90	1.80
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK) (Type TH)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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